

## ADG708/ADG709

### FEATURES

**1.8 V to 5.5 V Single Supply**  
 **$\pm 3$  V Dual Supply**  
**3  $\Omega$  On-Resistance**  
**0.75  $\Omega$  On-Resistance Flatness**  
**100 pA Leakage Currents**  
**14 ns Switching Times**  
**Single 8-to-1 Multiplexer ADG708**  
**Differential 4-to-1 Multiplexer ADG709**  
**16-Lead TSSOP Package**  
**Low Power Consumption**  
**TTL/CMOS-Compatible Inputs**

### APPLICATIONS

**Data Acquisition Systems**  
**Communication Systems**  
**Relay Replacement**  
**Audio and Video Switching**  
**Battery-Powered Systems**

### GENERAL DESCRIPTION

The ADG708 and ADG709 are low voltage, CMOS analog multiplexers comprising eight single channels and four differential channels respectively. The ADG708 switches one of eight inputs (S1–S8) to a common output, D, as determined by the 3-bit binary address lines A0, A1, and A2. The ADG709 switches one of four differential inputs to a common differential output as determined by the 2-bit binary address lines A0 and A1. An EN input on both devices is used to enable or disable the device. When disabled, all channels are switched OFF.

Low power consumption and operating supply range of 1.8 V to 5.5 V make the ADG708 and ADG709 ideal for battery-powered, portable instruments. All channels exhibit break-before-make switching action preventing momentary shorting when switching channels.

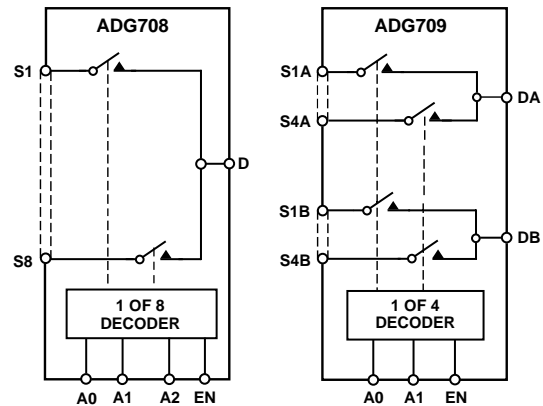
These switches are designed on an enhanced submicron process that provides low power dissipation yet gives high switching speed, very low on-resistance and leakage currents. On-resistance is in the region of a few ohms and is closely matched between switches and very flat over the full signal range. These parts can operate equally well as either Multiplexers or Demultiplexers, and have an input signal range that extends to the supplies.

The ADG708 and ADG709 are available in a 16-lead TSSOP package.

### REV. 0

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### FUNCTIONAL BLOCK DIAGRAMS



### PRODUCT HIGHLIGHTS

1. Single/Dual Supply Operation. The ADG708 and ADG709 are fully specified and guaranteed with 3 V and 5 V single supply and  $\pm 3$  V dual supply rails.
2. Low  $R_{ON}$  (3  $\Omega$  Typical).
3. Low Power Consumption ( $<0.01 \mu\text{W}$ ).
4. Guaranteed Break-Before-Make Switching Action.
5. Small 16-Lead TSSOP Package.

# ADG708/ADG709—SPECIFICATIONS<sup>1</sup> ( $V_{DD} = 5\text{ V} \pm 10\%$ , $V_{SS} = 0\text{ V}$ , $GND = 0\text{ V}$ , unless otherwise noted)

Parameter	B Version –40°C		C Version –40°C		Unit	Test Conditions/Comments
	+25°C	to +85°C	+25°C	to +85°C		
<b>ANALOG SWITCH</b>						
Analog Signal Range	0 V to $V_{DD}$		0 V to $V_{DD}$		V	
On-Resistance ( $R_{ON}$ )	3		3		$\Omega$ typ	$V_S = 0\text{ V to }V_{DD}$ , $I_{DS} = 10\text{ mA}$ ; Test Circuit 1
	4.5	5	4.5	5	$\Omega$ max	
On-Resistance Match Between Channels ( $\Delta R_{ON}$ )		0.4		0.4	$\Omega$ typ	
		0.8		0.8	$\Omega$ max	$V_S = 0\text{ V to }V_{DD}$ , $I_{DS} = 10\text{ mA}$
On-Resistance Flatness ( $R_{FLAT(ON)}$ )	0.75		0.75		$\Omega$ typ	$V_S = 0\text{ V to }V_{DD}$ , $I_{DS} = 10\text{ mA}$
		1.2		1.2	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>						
Source OFF Leakage $I_S$ (OFF)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_{DD} = 5.5\text{ V}$ $V_D = 4.5\text{ V/1 V}$ , $V_S = 1\text{ V/4.5 V}$ ; Test Circuit 2
		$\pm 20$	$\pm 0.1$	$\pm 0.3$	nA max	
Drain OFF Leakage $I_D$ (OFF)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_D = 4.5\text{ V/1 V}$ , $V_S = 1\text{ V/4.5 V}$ ; Test Circuit 3
		$\pm 20$	$\pm 0.1$	$\pm 0.75$	nA max	
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_D = V_S = 1\text{ V}$ , or $4.5\text{ V}$ , Test Circuit 4
		$\pm 20$	$\pm 0.1$	$\pm 0.75$	nA max	
<b>DIGITAL INPUTS</b>						
Input High Voltage, $V_{INH}$	2.4		2.4		V min	
Input Low Voltage, $V_{INL}$	0.8		0.8		V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005		0.005		$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
		$\pm 0.1$		$\pm 0.1$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	2		2		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>						
$t_{TRANSITION}$	14		14		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ , Test Circuit 5
		25		25	ns max	$V_{S1} = 3\text{ V/0 V}$ , $V_{SS} = 0\text{ V/3 V}$
Break-Before-Make Time Delay, $t_D$	8		8		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$
		1		1	ns min	$V_S = 3\text{ V}$ , Test Circuit 6
$t_{ON(EN)}$	14		14		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$
		25		25	ns max	$V_S = 3\text{ V}$ , Test Circuit 7
$t_{OFF(EN)}$	7		7		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$
		12		12	ns max	$V_S = 3\text{ V}$ , Test Circuit 7
Charge Injection	$\pm 3$		$\pm 3$		pC typ	$V_S = 2.5\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; Test Circuit 8
Off Isolation	–60		–60		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 10\text{ MHz}$
	–80		–80		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; Test Circuit 9
Channel-to-Channel Crosstalk	–60		–60		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 10\text{ MHz}$
	–80		–80		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; Test Circuit 10
–3 dB Bandwidth	55		55		MHz typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , Test Circuit 9
$C_S$ (OFF)	13		13		pF typ	
$C_D$ (OFF)						
ADG708	85		85		pF typ	
ADG709	42		42		pF typ	
$C_D$ , $C_S$ (ON)						
ADG708	96		96		pF typ	
ADG709	48		48		pF typ	
<b>POWER REQUIREMENTS</b>						
$I_{DD}$	0.001		0.001		$\mu\text{A}$ typ	$V_{DD} = 5.5\text{ V}$ Digital Inputs = 0 V or 5.5 V
		1.0		1.0	$\mu\text{A}$ max	

## NOTES

<sup>1</sup>Temperature range is as follows: B and C Versions: –40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

SPECIFICATIONS<sup>1</sup>(V<sub>DD</sub> = 3 V ± 10%, V<sub>SS</sub> = 0 V, GND = 0 V, unless otherwise noted)

Parameter	B Version		C Version		Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	+25°C	-40°C to +85°C		
<b>ANALOG SWITCH</b>						
Analog Signal Range		0 V to V <sub>DD</sub>		0 V to V <sub>DD</sub>	V	
On-Resistance (R <sub>ON</sub> )	8		8		Ω typ	V <sub>S</sub> = 0 V to V <sub>DD</sub> , I <sub>DS</sub> = 10 mA;
	11	12	11	12	Ω max	Test Circuit 1
On-Resistance Match Between Channels (ΔR <sub>ON</sub> )		0.4		0.4	Ω typ	V <sub>S</sub> = 0 V to V <sub>DD</sub> , I <sub>DS</sub> = 10 mA
		1.2		1.2	Ω max	
<b>LEAKAGE CURRENTS</b>						
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01		±0.01		nA typ	V <sub>DD</sub> = 3.3 V
		±20	±0.1	±0.3	nA max	V <sub>S</sub> = 3 V/1 V, V <sub>D</sub> = 1 V/3 V;
Drain OFF Leakage I <sub>D</sub> (OFF)	±0.01		±0.01		nA typ	Test Circuit 2
		±20	±0.1	±0.75	nA max	V <sub>S</sub> = 3 V/1 V, V <sub>D</sub> = 1 V/3 V;
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	±0.01		±0.01		nA typ	Test Circuit 3
		±20	±0.1	±0.75	nA max	V <sub>S</sub> = V <sub>D</sub> = 1 V or 3 V, Test Circuit 4
<b>DIGITAL INPUTS</b>						
Input High Voltage, V <sub>INH</sub>		2.0		2.0	V min	
Input Low Voltage, V <sub>INL</sub>		0.4		0.4	V max	
Input Current						
I <sub>INL</sub> or I <sub>INH</sub>	0.005		0.005		μA typ	V <sub>IN</sub> = V <sub>INL</sub> or V <sub>INH</sub>
		±0.1		±0.1	μA max	
C <sub>IN</sub> , Digital Input Capacitance	2		2		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>						
t <sub>TRANSITION</sub>	18		18		ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF, Test Circuit 5
		30		30	ns max	V <sub>S1</sub> = 2 V/0 V, V <sub>S2</sub> = 0 V/2 V
Break-Before-Make Time Delay, t <sub>D</sub>	8		8		ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF
		1		1	ns min	V <sub>S</sub> = 2 V, Test Circuit 6
t <sub>ON</sub> (EN)	18		18		ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF
		30		30	ns max	V <sub>S</sub> = 2 V, Test Circuit 7
t <sub>OFF</sub> (EN)	8		8		ns typ	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF
		15		15	ns max	V <sub>S</sub> = 2 V, Test Circuit 7
Charge Injection	±3		±3		pC typ	V <sub>S</sub> = 1.5 V, R <sub>S</sub> = 0 Ω, C <sub>L</sub> = 1 nF;
						Test Circuit 8
Off Isolation	-60		-60		dB typ	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 10 MHz
	-80		-80		dB typ	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 1 MHz;
						Test Circuit 9
Channel-to-Channel Crosstalk	-60		-60		dB typ	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 10 MHz
	-80		-80		dB typ	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, f = 1 MHz;
						Test Circuit 10
-3 dB Bandwidth	55		55		MHz typ	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF, Test Circuit 9
C <sub>S</sub> (OFF)	13		13		pF typ	
C <sub>D</sub> (OFF)						
ADG708	85		85		pF typ	
ADG709	42		42		pF typ	
C <sub>D</sub> , C <sub>S</sub> (ON)						
ADG708	96		96		pF typ	
ADG709	48		48		pF typ	
<b>POWER REQUIREMENTS</b>						
I <sub>DD</sub>	0.001		0.001		μA typ	V <sub>DD</sub> = 3.3 V
		1.0		1.0	μA max	Digital Inputs = 0 V or 3.3 V

## NOTES

<sup>1</sup>Temperature ranges are as follows: B and C Versions: -40°C to +85°C.<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# ADG708/ADG709—SPECIFICATIONS<sup>1</sup>

**DUAL SUPPLY** ( $V_{DD} = +3\text{ V} \pm 10\%$ ,  $V_{SS} = -3\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ )

Parameter	B Version -40°C		C Version -40°C		Unit	Test Conditions/Comments
	+25°C	to +85°C	+25°C	to +85°C		
<b>ANALOG SWITCH</b>						
Analogue Signal Range	$V_{SS}$ to $V_{DD}$		$V_{SS}$ to $V_{DD}$		V	$V_S = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10\text{ mA}$ ; Test Circuit 1
On-Resistance ( $R_{ON}$ )	2.5		2.5		$\Omega$ typ	
	4.5	5	4.5	5	$\Omega$ max	
On-Resistance Match Between Channels ( $\Delta R_{ON}$ )		0.4		0.4	$\Omega$ typ	$V_S = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10\text{ mA}$ ; $V_S = V_{SS}$ to $V_{DD}$ , $I_{DS} = 10\text{ mA}$
		0.8		0.8	$\Omega$ max	
On-Resistance Flatness ( $R_{FLAT(ON)}$ )	0.6		0.6		$\Omega$ typ	
		1.0		1.0	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>						
Source OFF Leakage $I_S$ (OFF)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_{DD} = +3.3\text{ V}$ , $V_{SS} = -3.3\text{ V}$ ; $V_S = +2.25\text{ V}/-1.25\text{ V}$ , $V_D = -1.25\text{ V}/+2.25\text{ V}$ ; Test Circuit 2
		$\pm 20$	$\pm 0.1$	$\pm 0.3$	nA max	
Drain OFF Leakage $I_D$ (OFF)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_S = +2.25\text{ V}/-1.25\text{ V}$ , $V_D = -1.25\text{ V}/+2.25\text{ V}$ ; Test Circuit 3
		$\pm 20$	$\pm 0.1$	$\pm 0.75$	nA max	
Channel ON Leakage $I_D$ , $I_S$ (ON)	$\pm 0.01$		$\pm 0.01$		nA typ	$V_S = V_D = +2.25\text{ V}/-1.25\text{ V}$ , Test Circuit 4
		$\pm 20$	$\pm 0.1$	$\pm 0.75$	nA max	
<b>DIGITAL INPUTS</b>						
Input High Voltage, $V_{INH}$	2.0		2.0		V min	$V_{IN} = V_{INL}$ or $V_{INH}$
Input Low Voltage, $V_{INL}$	0.4		0.4		V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005		0.005		$\mu\text{A}$ typ	
		$\pm 0.1$		$\pm 0.1$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	2		2		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>						
$t_{TRANSITION}$	14		14		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ , Test Circuit 5 $V_S = 1.5\text{ V}/0\text{ V}$ , Test Circuit 5
		25		25	ns max	
Break-Before-Make Time Delay, $t_D$	8		8		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ $V_S = 1.5\text{ V}$ , Test Circuit 6
		1		1	ns min	
$t_{ON(EN)}$	14		14		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ $V_S = 1.5\text{ V}$ , Test Circuit 7
		25		25	ns max	
$t_{OFF(EN)}$	8		8		ns typ	$R_L = 300\ \Omega$ , $C_L = 35\text{ pF}$ $V_S = 1.5\text{ V}$ , Test Circuit 7
		15		15	ns max	
Charge Injection	$\pm 3$		$\pm 3$		pC typ	$V_S = 0\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; Test Circuit 8
Off Isolation	-60		-60		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 10\text{ MHz}$ $R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; Test Circuit 9
	-80		-80		dB typ	
Channel-to-Channel Crosstalk	-60		-60		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 10\text{ MHz}$ $R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; Test Circuit 10
	-80		-80		dB typ	
-3 dB Bandwidth	55		55		MHz typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , Test Circuit 9
$C_S$ (OFF)	13		13		pF typ	
$C_D$ (OFF)						
ADG708	85		85		pF typ	
ADG709	42		42		pF typ	
$C_D$ , $C_S$ (ON)						
ADG708	96		96		pF typ	
ADG709	48		48		pF typ	
<b>POWER REQUIREMENTS</b>						
$I_{DD}$	0.001		0.001		$\mu\text{A}$ typ	$V_{DD} = 3.3\text{ V}$ Digital Inputs = 0 V or 3.3 V
		1.0		1.0	$\mu\text{A}$ max	
$I_{SS}$	0.001		0.001		$\mu\text{A}$ typ	$V_{SS} = -3.3\text{ V}$ Digital Inputs = 0 V or 3.3 V
		1.0		1.0	$\mu\text{A}$ max	

## NOTES

<sup>1</sup>Temperature range is as follows: B and C Versions: -40°C to +85°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

(T<sub>A</sub> = 25°C unless otherwise noted)

V <sub>DD</sub> to V <sub>SS</sub> .....	7 V
V <sub>DD</sub> to GND .....	-0.3 V to +7 V
V <sub>SS</sub> to GND .....	+0.3 V to -3.5 V
Analog Inputs <sup>2</sup> .....	V <sub>SS</sub> - 0.3 V to V <sub>DD</sub> + 0.3 V or 30 mA, Whichever Occurs First
Digital Inputs <sup>2</sup> .....	-0.3 V to V <sub>DD</sub> + 0.3 V or 30 mA, Whichever Occurs First
Peak Current, S or D .....	100 mA (Pulsed at 1 ms, 10% Duty Cycle max)
Continuous Current, S or D .....	30 mA
Operating Temperature Range	
Industrial (B, C Versions) .....	-40°C to +85°C
Storage Temperature Range .....	-65°C to +150°C
Junction Temperature .....	150°C

TSSOP Package, Power Dissipation .....	432 mW
θ <sub>JA</sub> Thermal Impedance .....	150.4°C/W
θ <sub>JC</sub> Thermal Impedance .....	27.6°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec) .....	215°C
Infrared (15 sec) .....	220°C

## NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup>Overtolerages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG708/ADG709 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



**Table I. ADG708 Truth Table**

A2	A1	A0	EN	Switch Condition
X	X	X	0	NONE
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

X = Don't Care

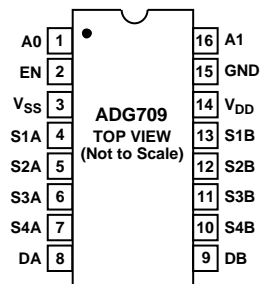
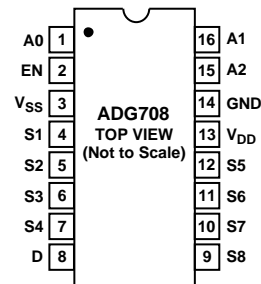
**Table II. ADG709 Truth Table**

A1	A0	EN	ON Switch Pair
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

X = Don't Care.

## PIN CONFIGURATIONS

### TSSOP



## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG708BRU	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG709BRU	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG708CRU	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG709CRU	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16

## TERMINOLOGY

$V_{DD}$	Most positive power supply potential.	$t_{ON} (EN)$	Delay time between the 50% and 90% points of the EN digital input and the switch “ON” condition.
$V_{SS}$	Most negative power supply in a dual supply application. In single supply applications, this should be tied to ground at the device.	$t_{OFF} (EN)$	Delay time between the 50% and 90% points of the EN digital input and the switch “OFF” condition.
GND	Ground (0 V) Reference.	$t_{OPEN}$	“OFF” time measured between the 80% points of both switches when switching from one address state to another.
S	Source Terminal. May be an input or output.	Off Isolation	A measure of unwanted signal coupling through an “OFF” switch.
D	Drain Terminal. May be an input or output.	Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
IN	Logic Control Input.	Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
$R_{ON}$	Ohmic resistance between D and S.	Bandwidth	The frequency at which the output is attenuated by 3 dBs.
$R_{FLAT(ON)}$	Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal range.	On Response	The frequency response of the “ON” switch.
$I_S (OFF)$	Source leakage current with the switch “OFF.”	On Loss	The loss due to the ON resistance of the switch.
$I_D (OFF)$	Drain leakage current with the switch “OFF.”	$V_{INL}$	Maximum input voltage for Logic “0.”
$I_D, I_S (ON)$	Channel leakage current with the switch “ON.”	$V_{INH}$	Minimum input voltage for Logic “1.”
$V_D (V_S)$	Analog voltage on terminals D, S.	$I_{INL} (I_{INH})$	Input current of the digital input.
$C_S (OFF)$	“OFF” switch source capacitance. Measured with reference to ground.	$I_{DD}$	Positive Supply Current.
$C_D (OFF)$	“OFF” switch drain capacitance. Measured with reference to ground.	$I_{SS}$	Negative Supply Current.
$C_D, C_S (ON)$	“ON” switch capacitance. Measured with reference to ground.		
$C_{IN}$	Digital Input Capacitance.		
$t_{TRANSITION}$	Delay time measured between the 50% and 90% points of the digital inputs and the switch “ON” condition when switching from one address state to another.		

# Typical Performance Characteristics—ADG708/ADG709

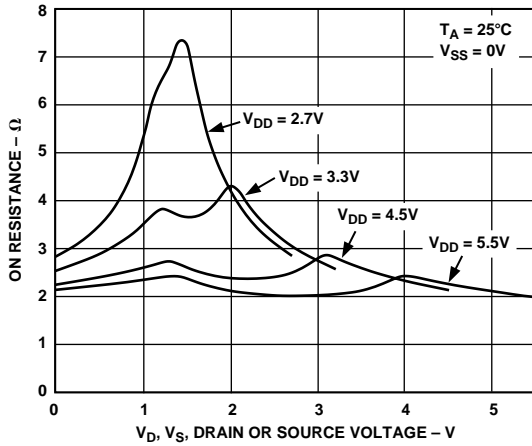


Figure 1. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Single Supply

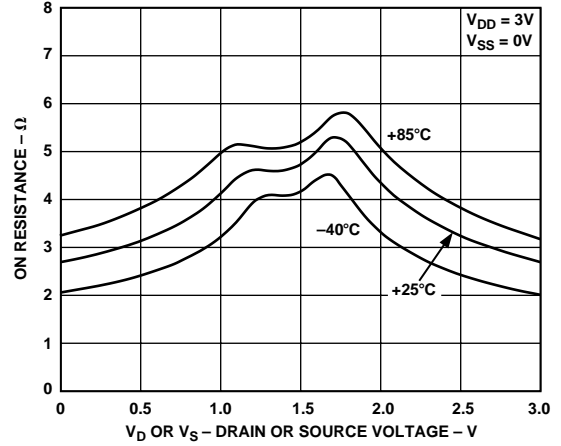


Figure 4. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Single Supply

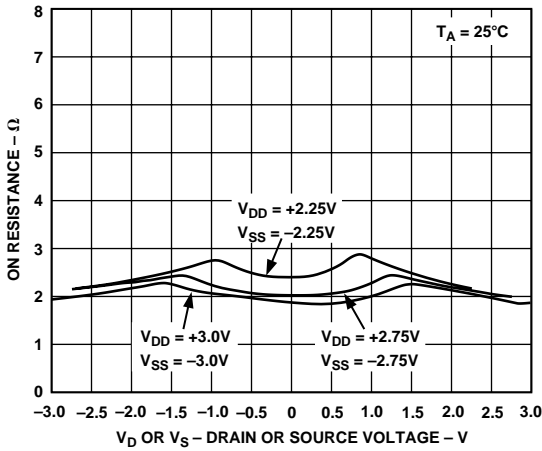


Figure 2. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Dual Supply

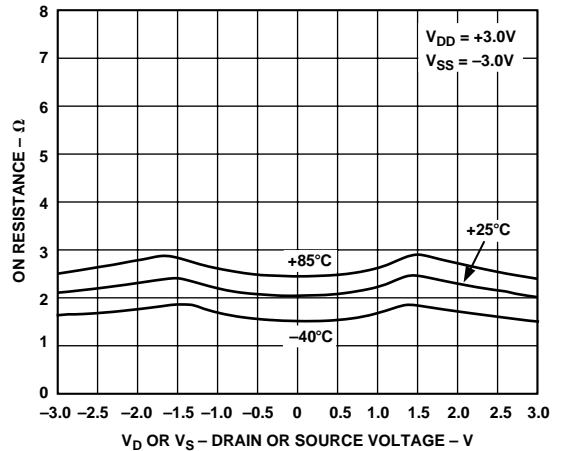


Figure 5. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Dual Supply

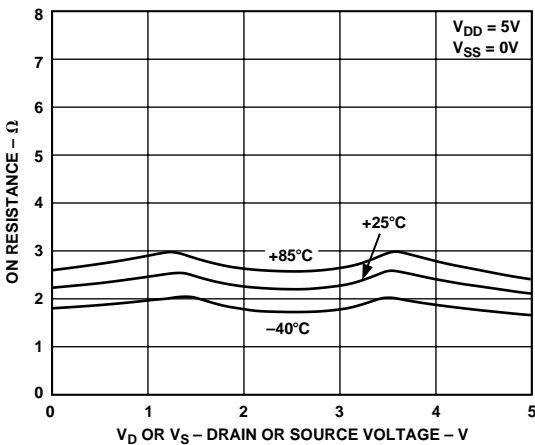


Figure 3. On Resistance as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures, Single Supply

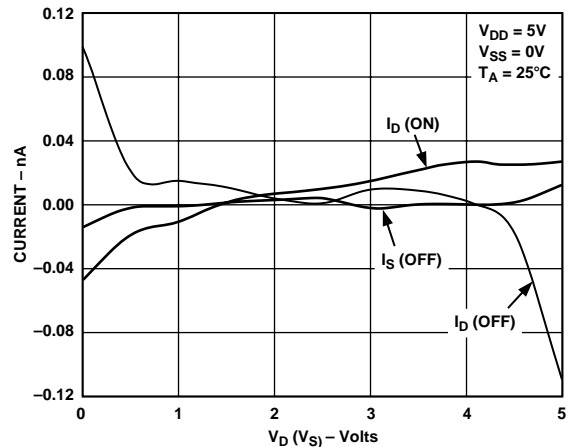


Figure 6. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

# ADG708/ADG709

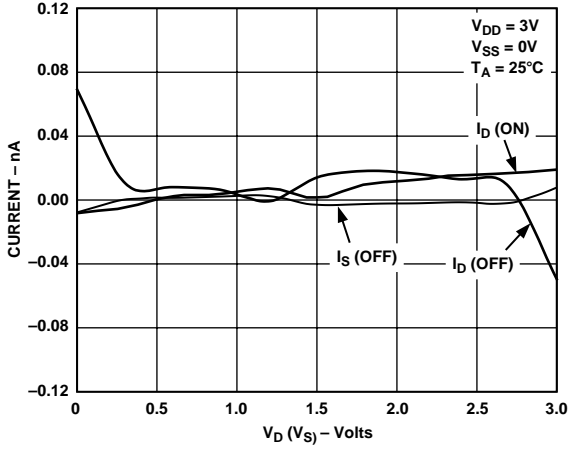


Figure 7. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

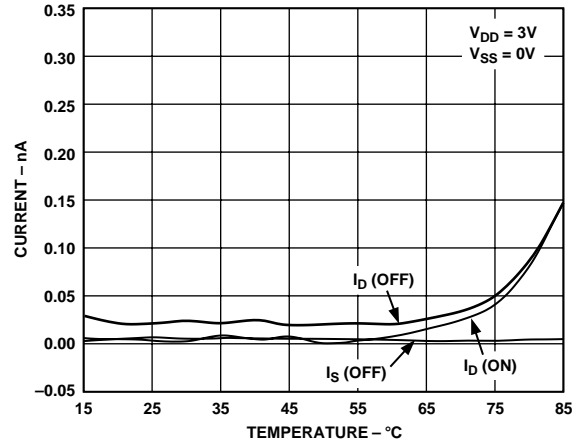


Figure 10. Leakage Currents as a Function of Temperature

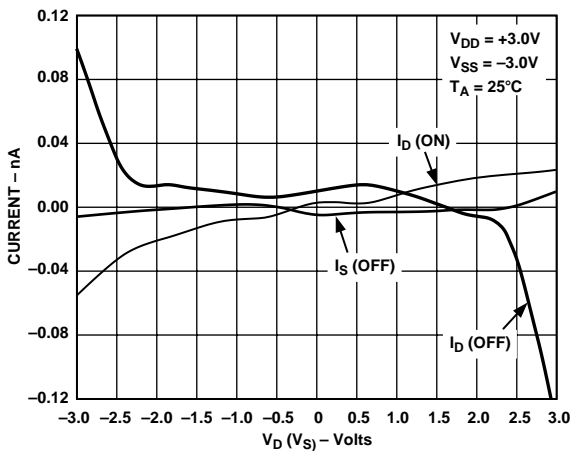


Figure 8. Leakage Currents as a Function of  $V_D$  ( $V_S$ )

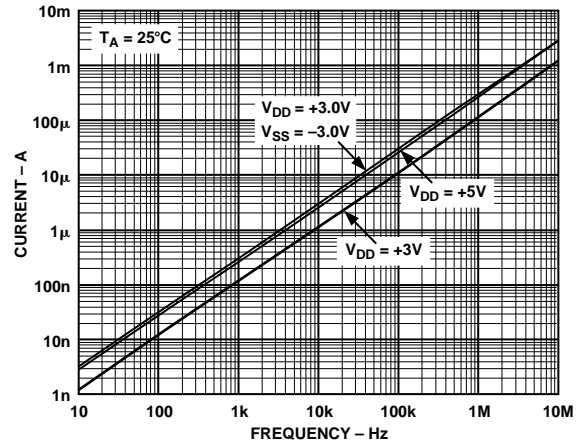


Figure 11. Supply Current vs. Input Switching Frequency

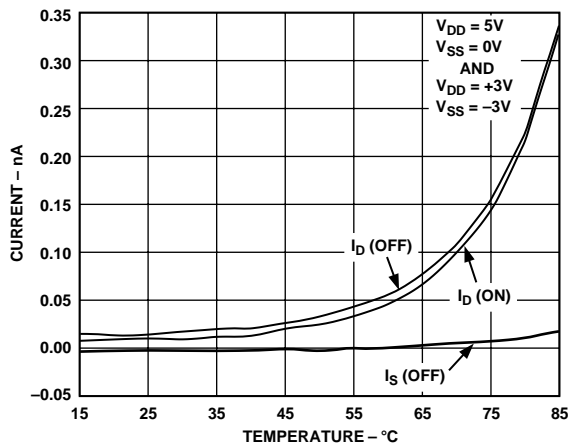


Figure 9. Leakage Currents as a Function of Temperature

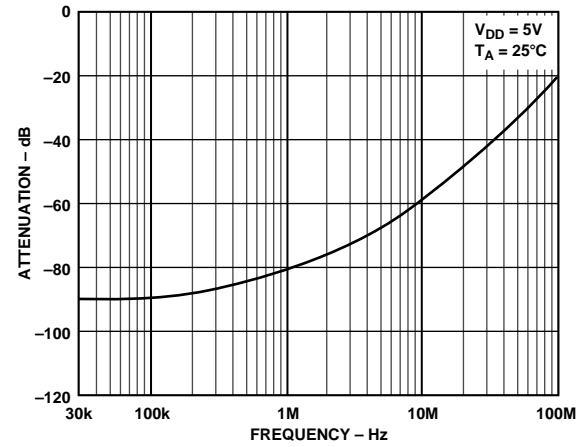


Figure 12. Off Isolation vs. Frequency



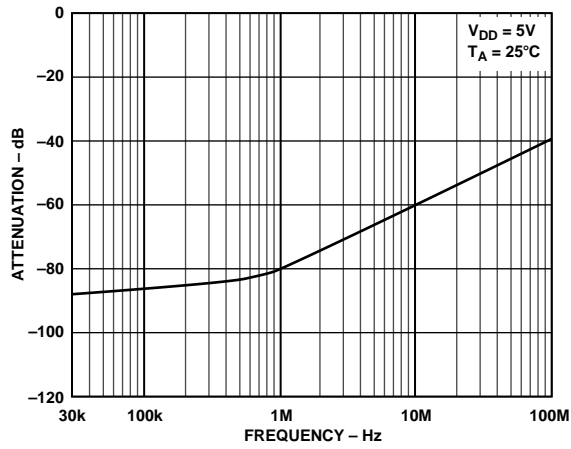


Figure 13. Crosstalk vs. Frequency

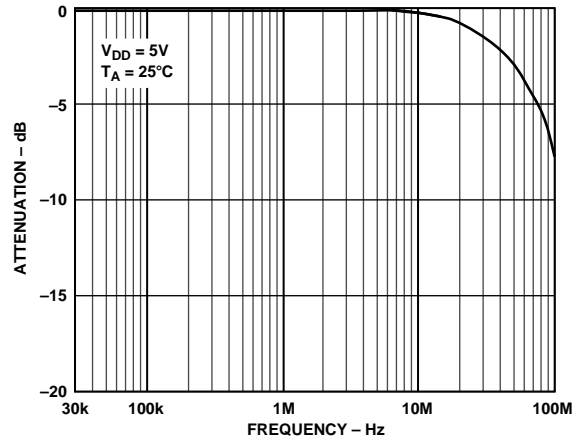


Figure 14. On Response vs. Frequency

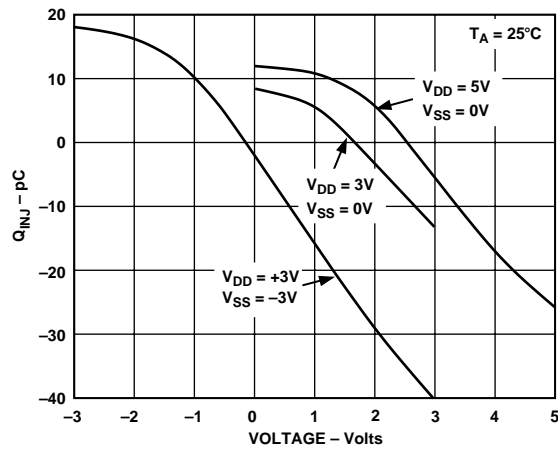
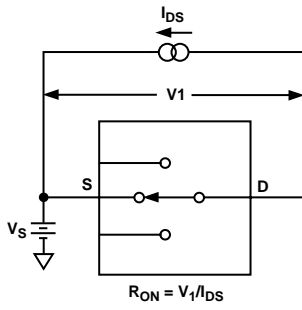


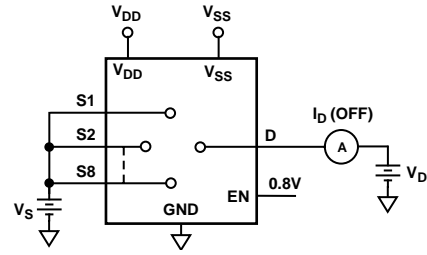
Figure 15. Charge Injection vs. Source Voltage

# ADG708/ADG709

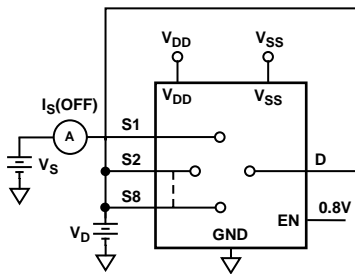
## Test Circuits



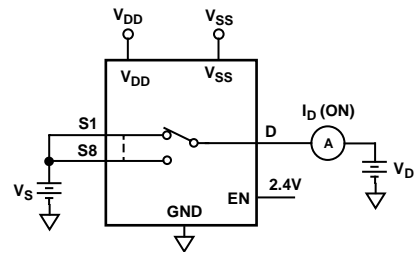
Test Circuit 1. On Resistance



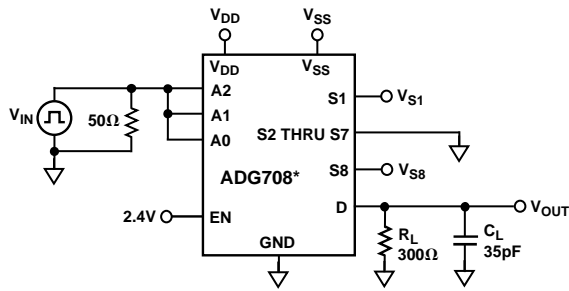
Test Circuit 3.  $I_D$  (OFF)



Test Circuit 2.  $I_S$  (OFF)

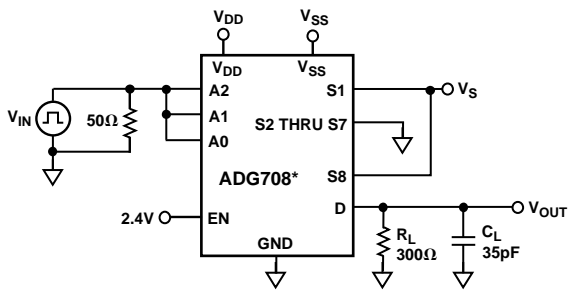
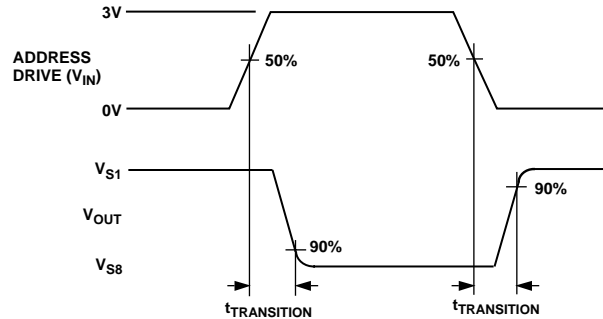


Test Circuit 4.  $I_D$  (ON)



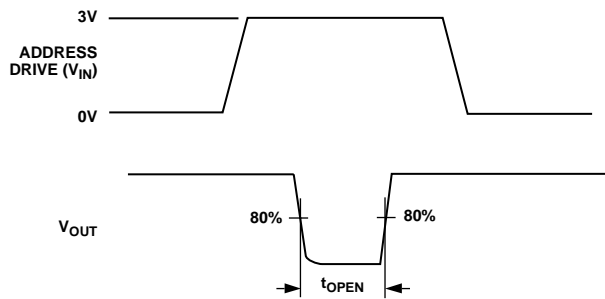
\* SIMILAR CONNECTION FOR ADG709

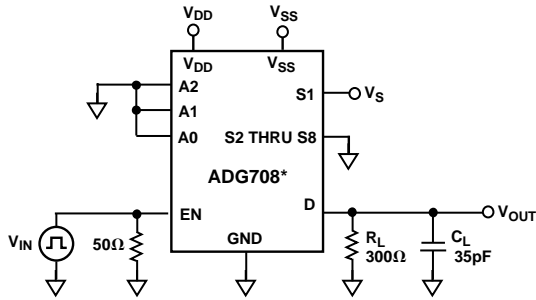
Test Circuit 5. Switching Time of Multiplexer,  $t_{TRANSITION}$



\* SIMILAR CONNECTION FOR ADG709

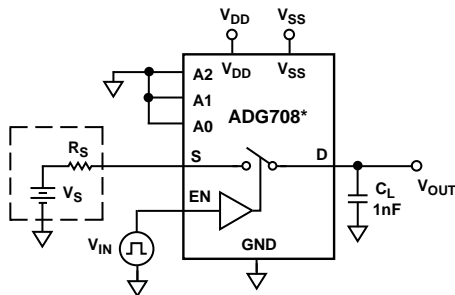
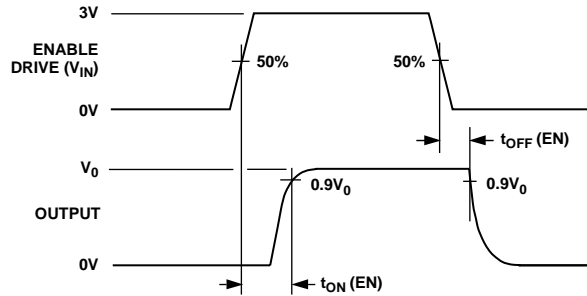
Test Circuit 6. Break-Before-Make Delay,  $t_{OPEN}$





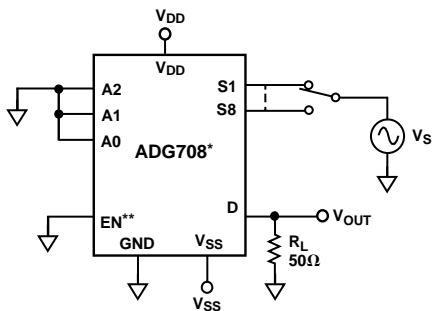
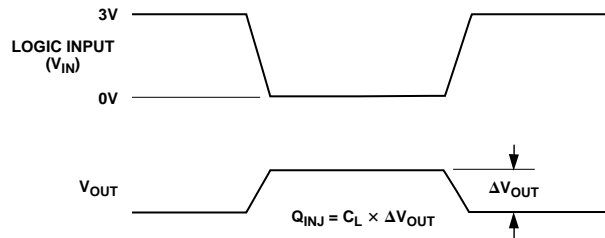
\* SIMILAR CONNECTION FOR ADG709

Test Circuit 7. Enable Delay,  $t_{ON}(EN)$ ,  $t_{OFF}(EN)$



\*SIMILAR CONNECTION FOR ADG709

Test Circuit 8. Charge Injection



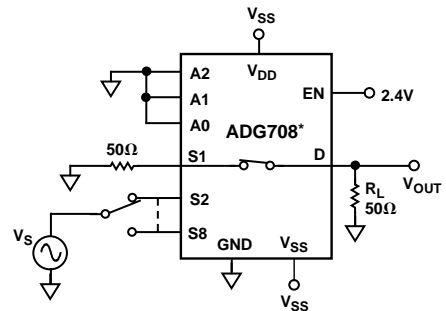
$$\text{OFF ISOLATION} = 20\text{LOG}_{10} \frac{V_{\text{OUT}}}{V_{\text{S}}}$$

$$\text{INSERTION LOSS} = 20\text{LOG}_{10} \left( \frac{V_{\text{OUT WITH SWITCH}}}{V_{\text{OUT WITHOUT SWITCH}}} \right)$$

\* SIMILAR CONNECTION FOR ADG709

\*\* CONNECT TO 2.4V FOR BANDWIDTH MEASUREMENTS

Test Circuit 9. OFF Isolation and Bandwidth



$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20\text{LOG}_{10} \frac{V_{\text{OUT}}}{V_{\text{S}}}$$

\* SIMILAR CONNECTION FOR ADG709

Test Circuit 10. Channel-to-Channel Crosstalk

### Power-Supply Sequencing

When using CMOS devices, care must be taken to ensure correct power-supply sequencing. Incorrect power-supply sequencing can result in the device being subjected to stresses beyond the maximum ratings listed in the data sheet. Digital and analog inputs should always be applied after power supplies and ground. For single supply operation,  $V_{SS}$  should be tied to GND as close to the device as possible.

# ADG708/ADG709

## OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

### 16-Lead TSSOP (RU-16)

